

MC74HCT125A

Quad 3-State Noninverting Buffer with LSTTL Compatible Inputs

High-Performance Silicon-Gate CMOS

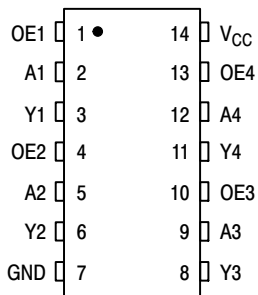
The MC74HCT125A is identical in pinout to the LS125. The device inputs are compatible with standard CMOS and LSTTL outputs.

The MC74HCT125A noninverting buffer is designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The devices have four separate output enables that are active-low.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the JEDEC Standard No. 7A Requirements
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- These are Pb-Free Devices

PIN ASSIGNMENT

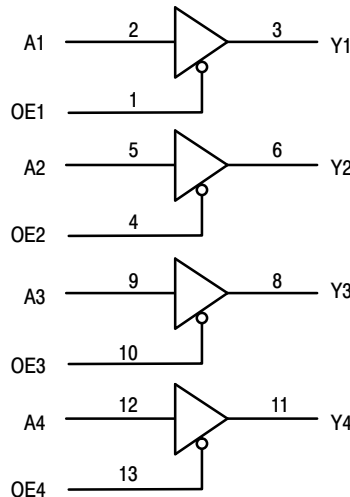


FUNCTION TABLE

HCT125A		
Inputs		Output
A	OE	Y
H	L	H
L	L	L
X	H	Z

LOGIC DIAGRAM

Active-Low Output Enables



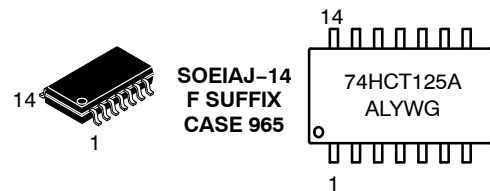
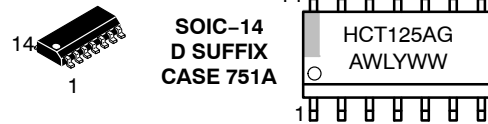
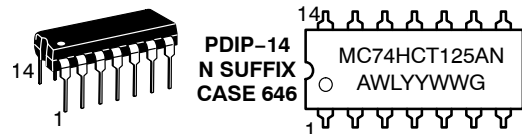
PIN 14 = V_{CC}
PIN 7 = GND



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MARKING DIAGRAMS



A = Assembly Location
L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G = Pb-Free Package
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

MC74HCT125A

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V	
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V	
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V	
I _{in}	DC Input Current, per Pin	± 20	mA	
I _{out}	DC Output Current, per Pin	± 35	mA	
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 75	mA	
P _D	Power Dissipation in Still Air	Plastic DIP†	750	mW
		SOIC Package†	500	
		TSSOP Package†	450	
T _{stg}	Storage Temperature	- 65 to + 150	°C	
T _L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C	

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

† Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C
 SOIC Package: - 7 mW/°C from 65° to 125°C
 TSSOP Package: - 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V	
T _A	Operating Temperature, All Package Types	- 55	+ 125	°C	
t _r , t _f	Input Rise and Fall Time (Figure 1)	V _{CC} = 2.0 V	0	1000	ns
		V _{CC} = 4.5 V	0	500	
		V _{CC} = 6.0 V	0	400	

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DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				- 55 to 25°C	≤ 85°C	≤ 125°C	
V _{IH}	Minimum High-Level Input Voltage	V _{out} = V _{CC} - 0.1 V I _{out} ≤ 20 μA	4.5 to 5.5	2.0	2.0	2.0	V
V _{IL}	Maximum Low-Level Input Voltage	V _{out} = 0.1 V I _{out} ≤ 20 μA	4.5 to 5.5	0.8	0.8	0.8	V
V _{OH}	Minimum High-Level Output Voltage	V _{in} = V _{IH} I _{out} ≤ 20 μA	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		V _{in} = V _{IH} I _{out} ≤ 6.0 mA	4.5	3.98	3.84	3.7	
V _{OL}	Maximum Low-Level Output Voltage	V _{in} = V _{IL} I _{out} ≤ 20 μA	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		V _{in} = V _{IL} I _{out} ≤ 6.0 mA	4.5	0.26	0.33	0.4	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	5.5	± 0.1	± 1.0	± 1.0	μA
I _{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GND	5.5	± 0.5	± 5.0	± 10	μA
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	5.5	4.0	40	160	μA

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6.0 ns, V_{CC} = 5.0 V ± 10%)

Symbol	Parameter	V _{CC} V	Guaranteed Limit			Unit
			- 55 to 25°C	≤ 85°C	≤ 125°C	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	5.0	18	23	27	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4)	5.0	24	30	36	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4)	5.0	18	23	27	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	5.0	12	15	18	ns
C _{in}	Maximum Input Capacitance	-	10	10	10	pF
C _{out}	Maximum 3-State Output Capacitance (Output in High-Impedance State)	-	15	15	15	pF
C _{PD}	Power Dissipation Capacitance (Per Buffer)*	Typical @ 25°C, V _{CC} = 5.0 V			pF	
		30				

*Used to determine the no-load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HCT125ANG	PDIP-14 (Pb-Free)	25 Units / Rail
MC74HCT125ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74HCT125ADR2G		2500 / Tape & Reel
MC74HCT125ADTG	TSSOP-14*	96 Units / Rail
MC74HCT125ADTR2G	TSSOP-14*	2500 / Tape & Reel
MC74HCT125AFG	SOEIAJ-14 (Pb-Free)	50 Units / Rail
MC74HCT125AFELG		2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb-Free.

MC74HCT125A

SWITCHING WAVEFORMS

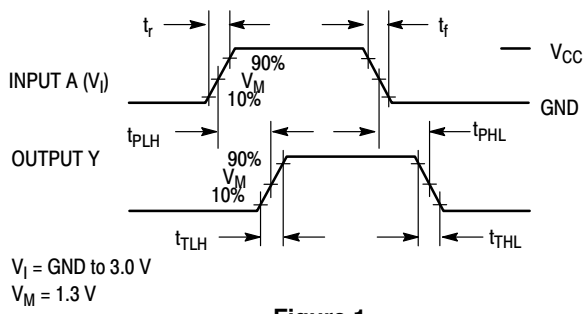


Figure 1.

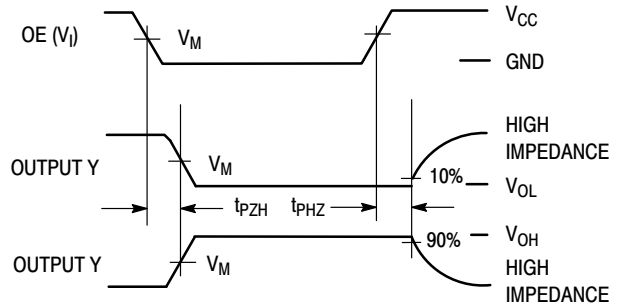
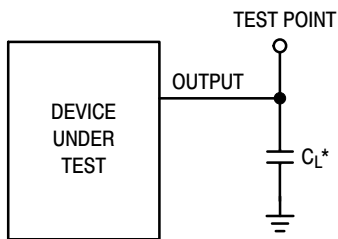
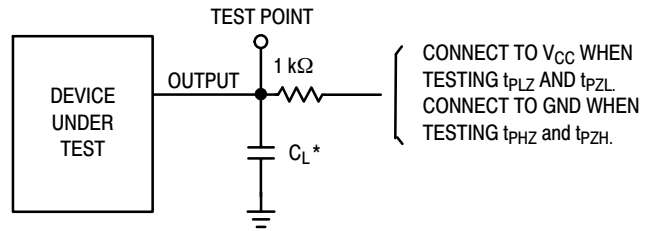


Figure 2.



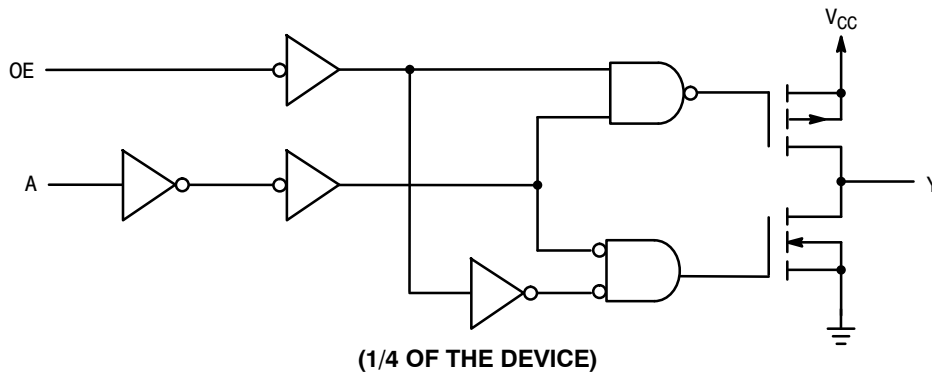
*Includes all probe and jig capacitance

Figure 3. Test Circuit



*Includes all probe and jig capacitance

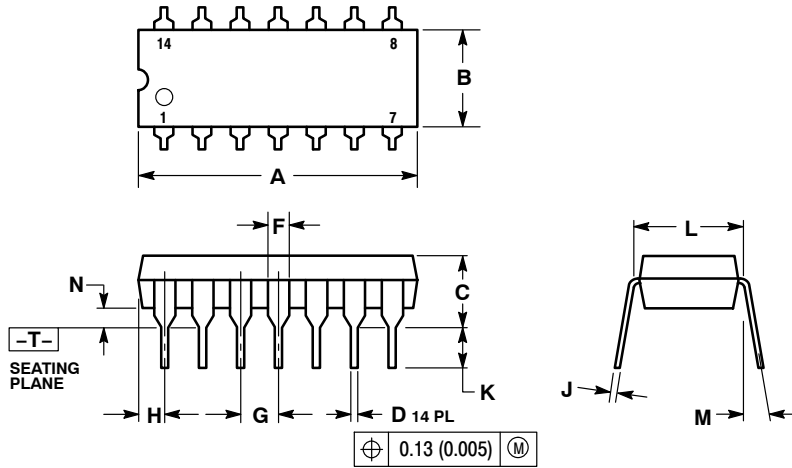
Figure 4. Test Circuit



MC74HCT125A

PACKAGE DIMENSIONS

PDIP-14
CASE 646-06
ISSUE P



NOTES:

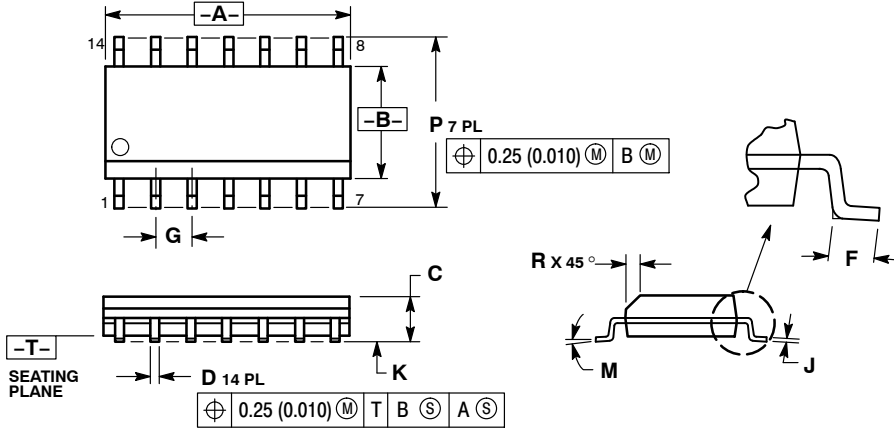
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	19.56
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M	--- 10°		--- 10°	
N	0.015	0.039	0.38	1.01

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PACKAGE DIMENSIONS

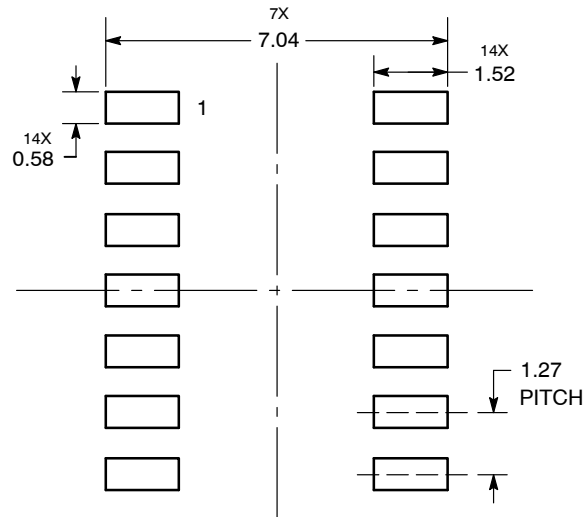
SOIC-14
CASE 751A-03
ISSUE J



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT*



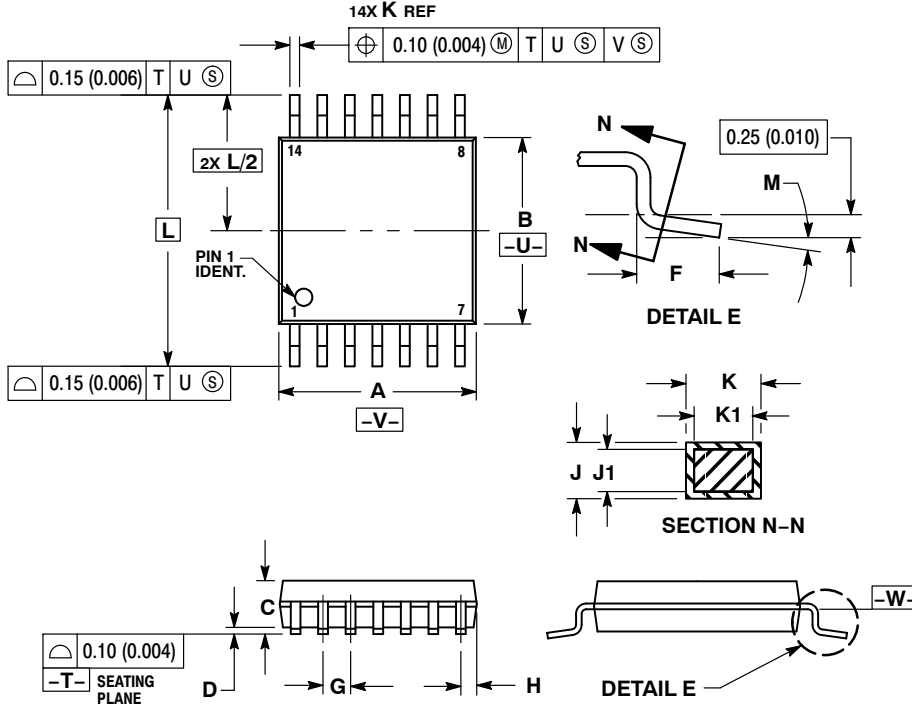
DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MC74HCT125A

PACKAGE DIMENSIONS

TSSOP-14
CASE 948G-01
ISSUE B

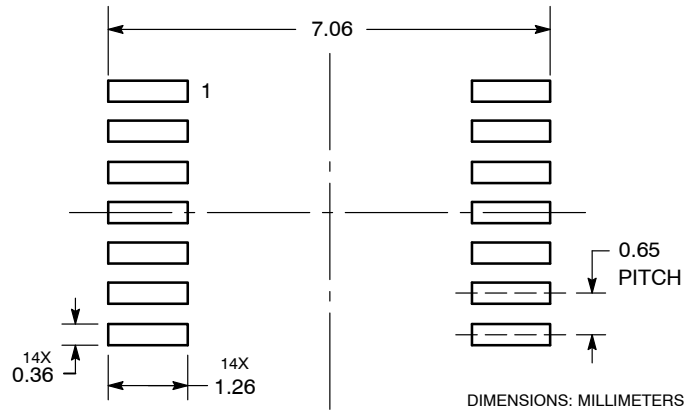


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

SOLDERING FOOTPRINT*

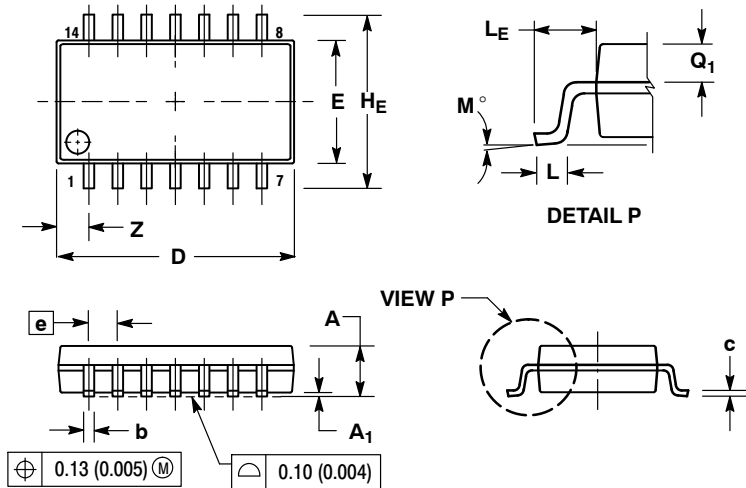


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MC74HCT125A

PACKAGE DIMENSIONS

SOEIAJ-14
CASE 965-01
ISSUE B



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H _E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L _E	1.10	1.50	0.043	0.059
M	0°	10°	0°	10°
Q ₁	0.70	0.90	0.028	0.035
Z	---	1.42	---	0.056

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